

**AMENDMENTS TO THE CLAIMS**

**This listing of claims will replace all prior versions and listings of claims in the application:**

**LISTING OF CLAIMS:**

**Claims 1-17 (canceled).**

18. (new): A high-strength, low-temperature-sintered ceramic composition having a structure comprising hexagonal  $\text{SrAl}_2\text{Si}_2\text{O}_8$  and an  $\text{Al}_2\text{O}_3$  crystal, said ceramic composition having a bending strength of 300 MPa or more.

19. (new): A high-strength, low-temperature-sintered ceramic composition comprising hexagonal  $\text{SrAl}_2\text{Si}_2\text{O}_8$  in an  $\text{Al}_2\text{O}_3$ - $\text{SiO}_2$ - $\text{SrO}$ -based matrix, which contains  $\text{Al}_2\text{O}_3$  crystal grains and has a bending strength of 300 MPa or more.

20. (new): The high-strength, low-temperature-sintered ceramic composition according to claim 19, wherein said matrix is an amorphous phase, in which hexagonal  $\text{SrAl}_2\text{Si}_2\text{O}_8$  is precipitated.

21. (new): The high-strength, low-temperature-sintered ceramic composition according to claim 19, wherein said matrix is substantially composed of a  $\text{SrAl}_2\text{Si}_2\text{O}_8$  crystal, at least part of which is hexagonal  $\text{SrAl}_2\text{Si}_2\text{O}_8$ .

22. (new): The high-strength, low-temperature-sintered ceramic composition according to claim 19, wherein said matrix contains monoclinic  $\text{SrAl}_2\text{Si}_2\text{O}_8$ .

PRELIMINARY AMENDMENT  
U.S. Application No.:

23. (new): A high-strength, low-temperature-sintered ceramic composition having a structure comprising a  $\text{SrAl}_2\text{Si}_2\text{O}_8$  crystal and an  $\text{Al}_2\text{O}_3$  crystal, said  $\text{SrAl}_2\text{Si}_2\text{O}_8$  crystal being composed of hexagonal  $\text{SrAl}_2\text{Si}_2\text{O}_8$  alone or hexagonal  $\text{SrAl}_2\text{Si}_2\text{O}_8$  and monoclinic  $\text{SrAl}_2\text{Si}_2\text{O}_8$ , a peak intensity ratio represented by  $I_{101} / (I_{101} + I_{002}) \times 100$  being 5% or more in an X-ray diffraction measurement by a Cu-K $\alpha$  line, wherein  $I_{101}$  represents a peak intensity of a (101) plane of the hexagonal  $\text{SrAl}_2\text{Si}_2\text{O}_8$ , and  $I_{002}$  represents a peak intensity of a (002) plane of the monoclinic  $\text{SrAl}_2\text{Si}_2\text{O}_8$ , and said ceramic composition having a bending strength of 300 MPa or more.

24. (new): The high-strength, low-temperature-sintered ceramic composition according to claim 23, wherein said peak intensity ratio is 50% or more.

25. (new): The high-strength, low-temperature-sintered ceramic composition according to claim 23, which has a structure comprising a matrix substantially composed of the  $\text{SrAl}_2\text{Si}_2\text{O}_8$  crystal, which contains  $\text{Al}_2\text{O}_3$  crystal grains, said  $\text{SrAl}_2\text{Si}_2\text{O}_8$  crystal being composed of hexagonal  $\text{SrAl}_2\text{Si}_2\text{O}_8$  alone or hexagonal  $\text{SrAl}_2\text{Si}_2\text{O}_8$  and monoclinic  $\text{SrAl}_2\text{Si}_2\text{O}_8$ , and a percentage of said hexagonal  $\text{SrAl}_2\text{Si}_2\text{O}_8$  in said  $\text{SrAl}_2\text{Si}_2\text{O}_8$  crystal being 60% or more, and said ceramic composition having a bending strength of 400 MPa or more.

26. (new): The high-strength, low-temperature-sintered ceramic composition according to claim 18, wherein said  $\text{Al}_2\text{O}_3$  crystal grains have an average diameter of 1  $\mu\text{m}$  or less.

27. (new): The high-strength, low-temperature-sintered ceramic composition according to claim 18, wherein it comprises (a) 100% by mass of main components comprising 10-60% by

PRELIMINARY AMENDMENT  
U.S. Application No.:

mass of Al (as  $\text{Al}_2\text{O}_3$ ), 25-60% by mass of Si (as  $\text{SiO}_2$ ) and 7.5-50% by mass of Sr (as SrO), (b) auxiliary components comprising at least one selected from the group consisting of 0.1-10% by mass of Bi (as  $\text{Bi}_2\text{O}_3$ ), 0.1-5% by mass of Na (as  $\text{Na}_2\text{O}$ ), 0.1-5% by mass, of K (as  $\text{K}_2\text{O}$ ) and 0.1-5% by mass of Co (as CoO), and at least one selected from the group consisting of 0.01-5% by mass of Cu (as CuO), 0.01-5% by mass of Mn (as  $\text{MnO}_2$ ), 0.01-5% by mass of Ag and 0.01-2% by mass of Zr (as  $\text{ZrO}_2$ ), and (c) inevitable impurities.

28. (new): The high-strength, low-temperature-sintered ceramic composition according to claim 18, wherein it comprises (a) 100% by mass of main components comprising 10-60% by mass of Al (as  $\text{Al}_2\text{O}_3$ ), 25-60% by mass of Si (as  $\text{SiO}_2$ ), 7.5-50% by mass of Sr (as SrO) and 20% or less by mass of Ti (as  $\text{TiO}_2$ ), (b) auxiliary components comprising at least one selected from the group consisting of 0.1-10% by mass of Bi (as  $\text{Bi}_2\text{O}_3$ ), 0.1-5% by mass of Na (as  $\text{Na}_2\text{O}$ ), 0.1-5% by mass of K (as  $\text{K}_2\text{O}$ ) and 0.1-5% by mass of Co (as CoO), and at least one selected from the group consisting of 0.01-5% by mass of Cu (as CuO), 0.01-5% by mass of Mn (as  $\text{MnO}_2$ ), 0.01-5% by mass of Ag and 0.01-2% by mass of Zr (as  $\text{ZrO}_2$ ), and (c) inevitable impurities.

29. (new): The high-strength, low-temperature-sintered ceramic composition according to claim 18, wherein it comprises 10-60% by mass of Al (as  $\text{Al}_2\text{O}_3$ ), 25-60% by mass of Si (as  $\text{SiO}_2$ ), 7.5-50% by mass of Sr (as SrO), and inevitable impurities.

30. (new): A method for producing the high-strength, low-temperature-sintered ceramic composition recited in claim 18, by sintering a ceramic green body comprising aluminum oxide,

PRELIMINARY AMENDMENT  
U.S. Application No.:

silicon oxide and strontium oxide, or aluminum oxide, silicon oxide, strontium oxide and titanium oxide as main starting materials, under such temperature and time conditions that a ratio of hexagonal  $\text{SrAl}_2\text{Si}_2\text{O}_8$  in a  $\text{SrAl}_2\text{Si}_2\text{O}_8$  crystal formed in a ceramic structure becomes 5% or more.

31. (new): A laminated electronic part comprising pluralities of dielectric layers made of the high-strength, low-temperature-sintered ceramic composition recited in claim 18, each of said dielectric layers being provided with a conductive pattern of a low-melting-point metal.

32. (new): The laminated electronic part according to claim 31, wherein said low-melting-point metal is silver, copper, gold or an alloy thereof.

33. (new): The laminated electronic part according to claim 31, wherein said conductive pattern constitutes an inductance element and/or a capacitance element.

34. (new): The laminated electronic part according to claim 31, onto which at least one selected from the group consisting of an inductance element, a capacitance element, a switching element and a filter element is mounted.